

**KABARAK**



**UNIVERSITY**

**UNIVERSITY EXAMINATIONS  
2010/2011 ACADEMIC YEAR  
FOR THE DEGREE OF BACHELOR OF COMPUTER  
SCIENCE**

**COURSE CODE: PHYS 120**

**COURSE TITLE: BASIC ELECTRONICS**

**STREAM: Y1S2**

**DAY: FRIDAY**

**TIME: 2.00 – 4.00 P.M.**

**DATE: 18/03/2011**

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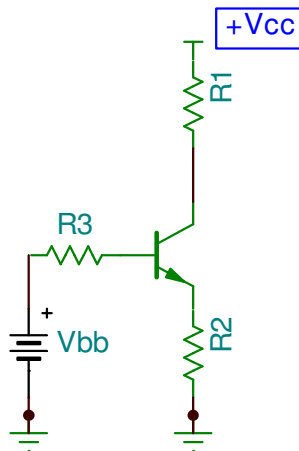
**INSTRUCTIONS:**

*Answer question ONE and any other TWO*

**PLEASE TURN OVER**

**Question 1 (30 marks)**

- a) Name the main charge carriers in
- (i) Metals (1 mark)
  - (ii) Semiconductors (1 mark)
- b) Describe the operation of a full-wave rectifier (5 marks)
- c) List 2 disadvantages of negative feedback in amplifiers. (2 marks)
- d) For the circuit shown below,  $R_1 = 3k$ ,  $R_3 = 200k$ ,  $R_2 = 500$  ohms,  $\beta = 100$ ,  $V_{BE} = 0.7$  V,  $V_{bb} = 5V$  and  $V_{CC} = 14$  V. Find the transistor currents  $I_B$  and  $I_C$ . (5 marks)



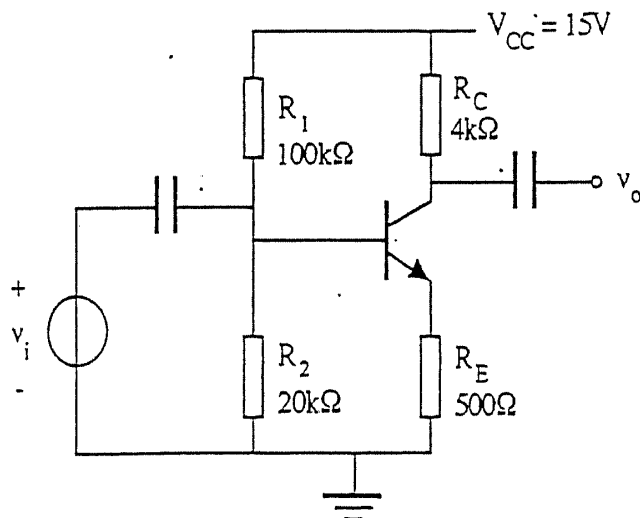
- e) Explain how a BJT can act as a switch (2 marks)
- f) Give arbitrary base and collector I/V characteristics for an npn transistor in the active region starting with  $V_{BE} = 0$  V. (2 marks)
- g) Briefly explain the following methods of pn junction formation
- (i) Grown junction (2 marks)
  - (ii) Alloying (2 marks)
- h) With aid of diagram, explain how an p-type material can be achieved (4 marks)
- i) State why a FET is called a unipolar device. (1 marks)
- j) State the four possible operating regimes of a BJT and give the required biasing conditions (6 marks)
- k) Explain the term thermal runaway and how it brings about transistor failure. (2 marks)

**Question 2 (20 marks)**

- a) With regard to feedback amplifiers, define the following terms:
- i) Open loop gain (1 mark)
  - ii) Closed loop gain (1 mark)
  - iii) Round trip gain (1 mark)
- b) Draw a black box representation of an amplifier with feedback and show how quantitatively that feedback reduces gain sensitivity. (8 marks)
- c) i) state the criteria for oscillation to occur in a circuit (2 marks)
- ii) Draw a circuit diagram of a Colpitts oscillator and derive its resonance frequency (7 marks)

**Question 3 (20 marks)**

- a) i) Define transistor biasing. (1 mark)
- ii) State the advantage of potential divider bias method over base bias (2 marks)
- iii) Draw a single stage BJT circuit employing base biasing and show that the  $I_C$  current for a base bias circuit is likely to be unstable. Provide the reason for instability. (7 marks)
- b) The circuit below shows a single stage transistor amplifier.
- i) Determine the quiescent voltage  $V_{CQ}$  and quiescent collector current  $I_{CQ}$ . (use  $\beta = 100$ ,  $V_{BE} = 0.6$  V) (5 marks)
- ii) Sketch the output characteristics ( $I_C$  versus  $V_{CE}$ ) and the load line. (5marks)



**Question 4 (20 marks)**

- a) State the functional differences between the following family of FET devices: Depletion Mode MOSFET and Enhancement Mode MOSFET. (3 marks)
- b) With the aid of a diagram, explain how the Gate voltage controls current flow in a JFET. (5 marks)
- c) For  $V_{gs} = 0$ , sketch the Drain current versus  $V_{DS}$  curve. Mark and explain the following:  
i)  $I_{DSS}$   
ii)  $V_p$   
iii) Breakdown region  
iv) Ohmic region (8 marks)
- d) The circuit below shows a gate-biased JFET amplifier. Determine the Q - point values for the gate biasing circuit if  $V_{GG} = -5\text{ V}$ ,  $V_{GS(off)} = -7\text{ V}$ ,  $I_{DSS} = 9\text{ mA}$ ,  $V_{DD} = 5\text{ V}$ , and  $R_D = 500\ \Omega$ . (4 marks)

